GSMBT4403

PNP EPITAXIAL PLANAR TRANSISTOR

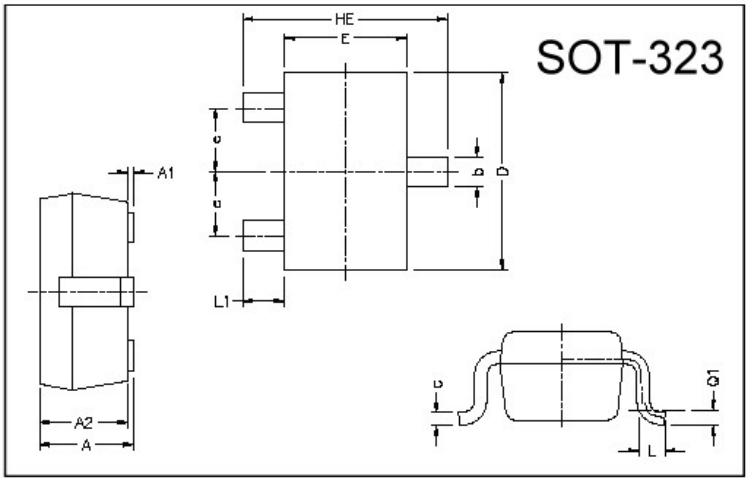
Description

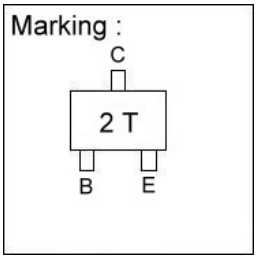
The GSMBT4403 is designed for general purpose switching and amplifier applications.

Features

- Complementary to GSMBT4401
- High DC Current Gain: 100-300 at 150mA

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

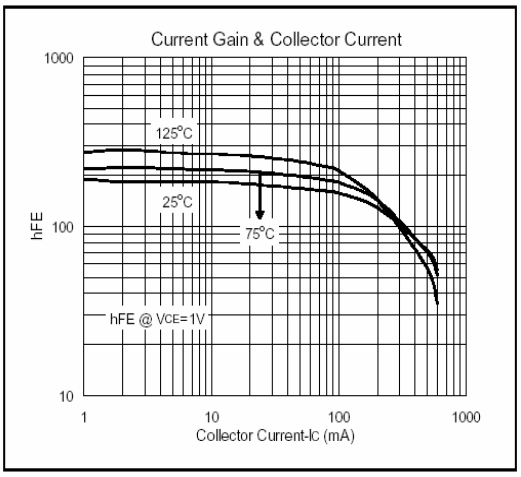
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage at Ta=25℃	VCBO	-40	V
Collector to Emitter Voltage at Ta=25℃	VCEO	-40	V
Emitter to Base Voltage at Ta=25℃	VEBO	-5	V
Collector Current at Ta=25℃	IC	-600	mA
Total Power Dissipation at Ta=25℃	PD	225	mW

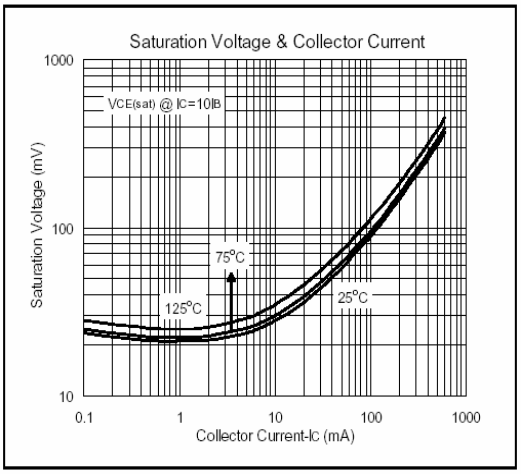
Characteristics at Ta = 25℃

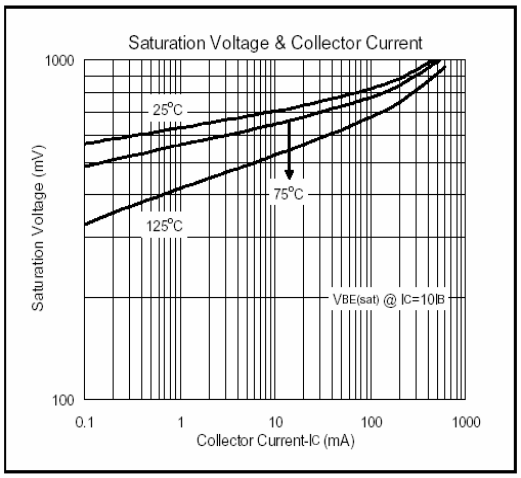
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-40	-	-	V	I_C=-100uA
BV_{CEO}	-40	-	-	V	I_C=-1mA
BV_{EBO}	-5	-	-	V	I_E=-10uA
I_{CEX}	-	-	-100	nA	V_{CE}=-35V, V_{BE}=-0.4V
*$V_{CE(sat)1}$	-	-	-400	mV	I_C=-150mA, I_B=-15mA
*$V_{CE(sat)2}$	-	-	-750	mV	I_C=-500mA, I_B=-50mA
*$V_{BE(sat)1}$	-	-	-950	mV	I_C=-150mA, I_B=-15mA
*$V_{BE(sat)2}$	-	-	-1.3	V	I_C=-500mA, I_B=-50mA
*h_{FE1}	30	-	-		V_{CE}=-1V, I_C=-0.1mA
*h_{FE2}	60	-	-		V_{CE}=-1V, I_C=-1mA
*h_{FE3}	100	-	-		V_{CE}=-1V, I_C=-10mA
*h_{FE4}	100	-	300		V_{CE}=-2V, I_C=-150mA
*h_{FE5}	20	-	-		V_{CE}=-2V, I_C=-500mA
fT	200	-	-	MHz	V_{CE}=-10V, I_C=-20mA, f=100MHz
Cob	-	-	8.5	pF	V_{CE}=-10V, f=1MHz

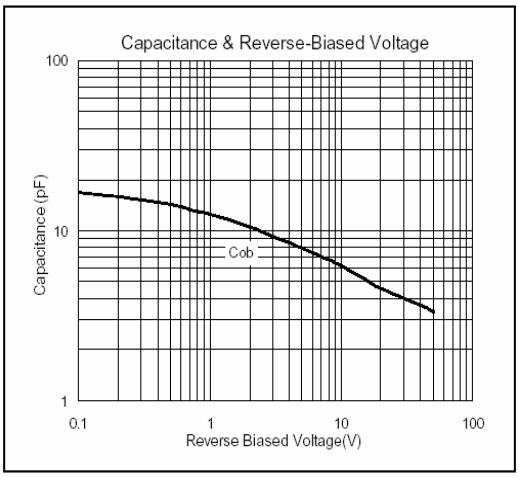
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

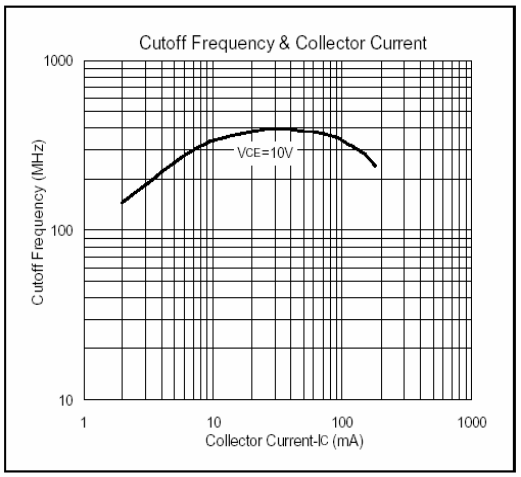
Characteristics Curve

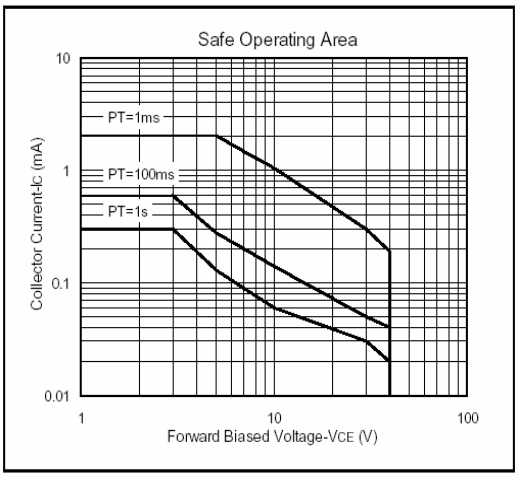












Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165